

Attorney's Docket No. 1232-4421US1

**PATENT** 

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants:

UEHARA et al.

Serial No.:

09/664,715

September 19, 2000

Group Art

1765

Examiner:

Kin Chan Chen

Confirmation

1475

For

Filed

WAFER PROCESSING APPARATUS, WAFER PROCESSING METHOD,

AND SEMICONDUCTOR SUBSTRATE FABRICATION METHOD

## PRELIMINARY AMENDMENT

## **BOX RCE**

Commissioner for Patents Washington, D.C. 20231

Sir:

In response to the Notice of Allowance and Notice of Allowability mailed January 9, 2002, Applicants hereby submit the Preliminary Amendment along with a Request for Continued Examination (RCE).

Prior to examination, please enter this Preliminary Amendment and amend the patent application as follows:

## **IN THE CLAIMS:**

Please add claims 40 and 41 as follows:

-40. (New) A semiconductor substrate fabrication method, comprising:

completely dipping a substrate on which a porous layer is exposed into an etching

solution; and

removing the porous layer of the substrate with the etching solution while rotating the

substrate.

04/02/2002 CHEHYEN 00000067 09664715

02 FC:102

164.00 CD

33281 v1

1